0.5W X/Ku-Band Power Amplifier 8.0-12.5 GHz

Preliminary Information

MAAPGM0034-DIE

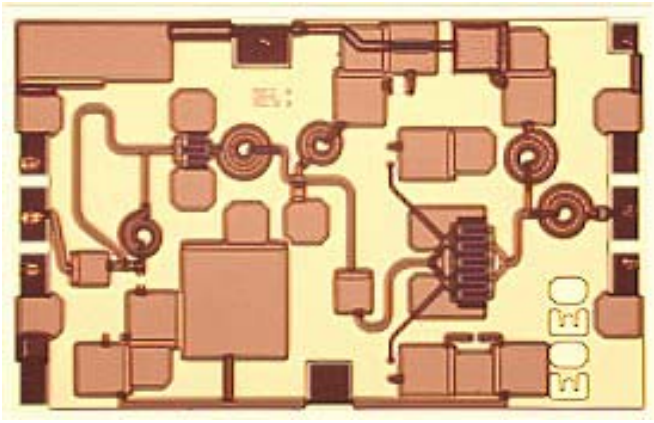
Features

- 8.0-12.5 GHz Operation
- 0.5 Watt Saturated Output Power Level
- Variable Drain Voltage (4-10V) Operation
- Self-Aligned MSAG® MESFET Process

Primary Applications

- Point-to-Point Radio
- Weather Radar
- Military Radar

8.0-12.5 GHz GaAs MMIC Amplifier



Description

The MAAPGM0034-Die is a 2-stage 0.5 W power amplifier with on-chip bias networks. This product is fully matched to 50 ohms on both the input and output. It can be used as a power amplifier stage or as a driver stage in high power applications.

Each device is 100% RF tested on wafer to ensure performance compliance. The part is fabricated using M/A-COM's repeatable, high performance and highly reliable GaAs Multifunction Self-Aligned Gate (MSAG®) MESFET Process. This process provides polyimide scratch protection.

Electrical Characteristics: T_B = 40°C[1], Z_0 = 50Ω, V_{DD} = 10V, V_{GG} = -2V, P_{in} = 18 dBm

Parameter	Symbol	Typical	Units
Bandwidth	f	8.0-12.5	GHz
Output Power	P_{OUT}	28	dBm
Power Added Efficiency	PAE	35	%
1-dB Compression Point	P1dB	26	dBm
Small Signal Gain	G	15	dB
Input VSWR	Input VSWR	2:1	
Gate Current	I_{GG}	< 2	mA
Drain Current	I_{DD}	< 200	mA
Output Third Order Intercept	OTOI	33	dBm
Noise Figure	NF	8	dB
2nd Harmonic	2f	-28	dBc
3rd Harmonic	3f	-35	dBc

1. T_B = MMIC Base Temperature

0.5W X/Ku-Band Power Amplifier MAAPGM0034-DIE

Maximum Operating Conditions [1]

Parameter	Symbol	Absolute Maximum	Units
Input Power	P_{IN}	21.0	dBm
Drain Supply Voltage	V_{DD}	+12.0	V
Gate Supply Voltage	V_{GG}	-3.0	V
Quiescent Drain Current (No RF)	I_{DQ}	190	mA
Quiescent DC Power Dissipated (No RF)	P_{DISS}	1.2	W
Junction Temperature	T_J	180	°C
Storage Temperature	T_{STG}	-55 to +150	°C

1. Operation outside of these ranges may reduce product reliability. Operation at other than typical values may result in performance outside guranteed limits.

Recommended Operating Conditions

Characteristic	Symbol	Min	Typ	Max	Unit
Drain Voltage	V_{DD}	4.0	10.0	10.0	V
Gate Voltage	V_{GG}	-2.3	-2.0	-1.5	V
Input Power	P_{IN}		18.0	19.0	dBm
Junction Temperature	T_J			150	°C
Thermal Resistance	Θ_{JC}		64.1		°C/W
MMIC Base Temperature	T_B			Note 2	°C

2. Maximum MMIC Base Temperature = 150°C —Θ_{JC}* V_{DD} * I_{DQ}

Operating Instructions

This device is static sensitive. Please handle with care. To operate the device, follow these steps.

1. Apply V_{GG} = -2 V, V_{DD}= 0 V.
2. Ramp V_{DD} to desired voltage, typically 10.0 V.
3. Adjust V_{GG} to set I_{DQ}, (approximately @ –2 V).
4. Set RF input.
5. Power down sequence in reverse. Turn gate voltage off last.

ATTENTION
Static-Sensitive Devices
Handling Precautions Required

Specifications subject to change without notice.

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Visit www.macom.com for additional data sheets and product information.

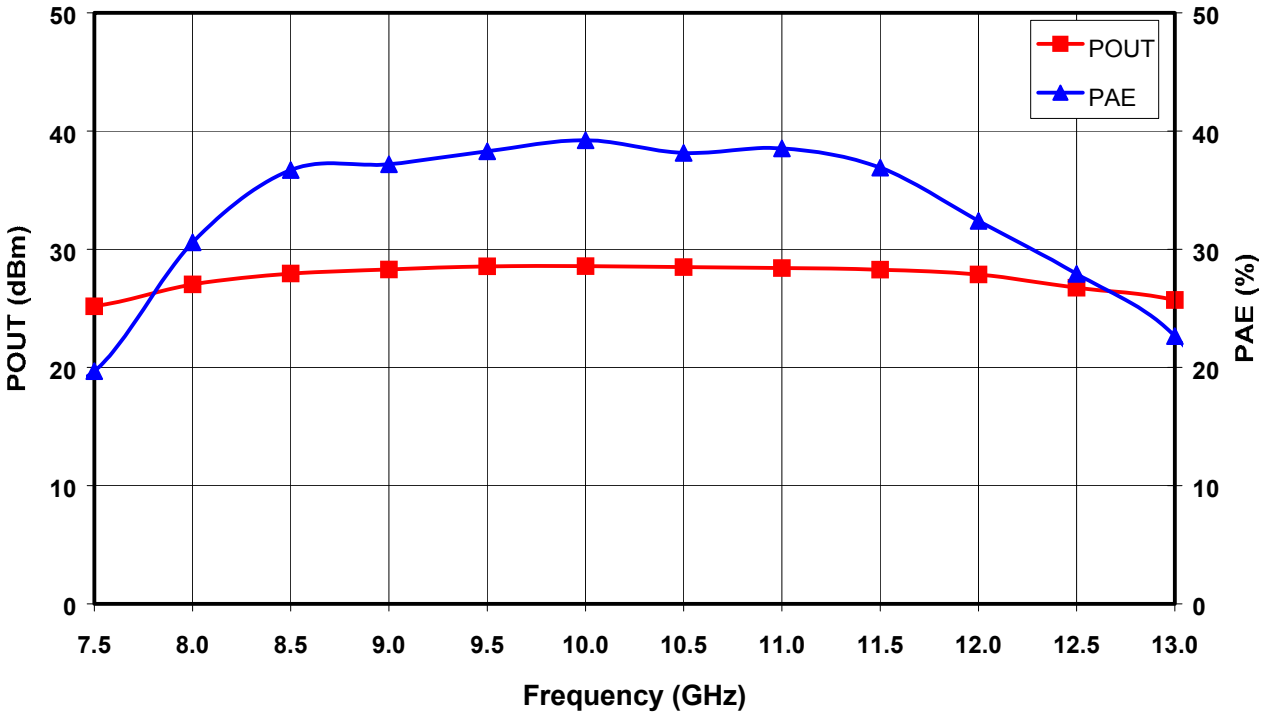

Figure 1. Output Power and Power Added Efficiency vs. Frequency at V_{DD} = 10V and P_{in} = 18 dBm.

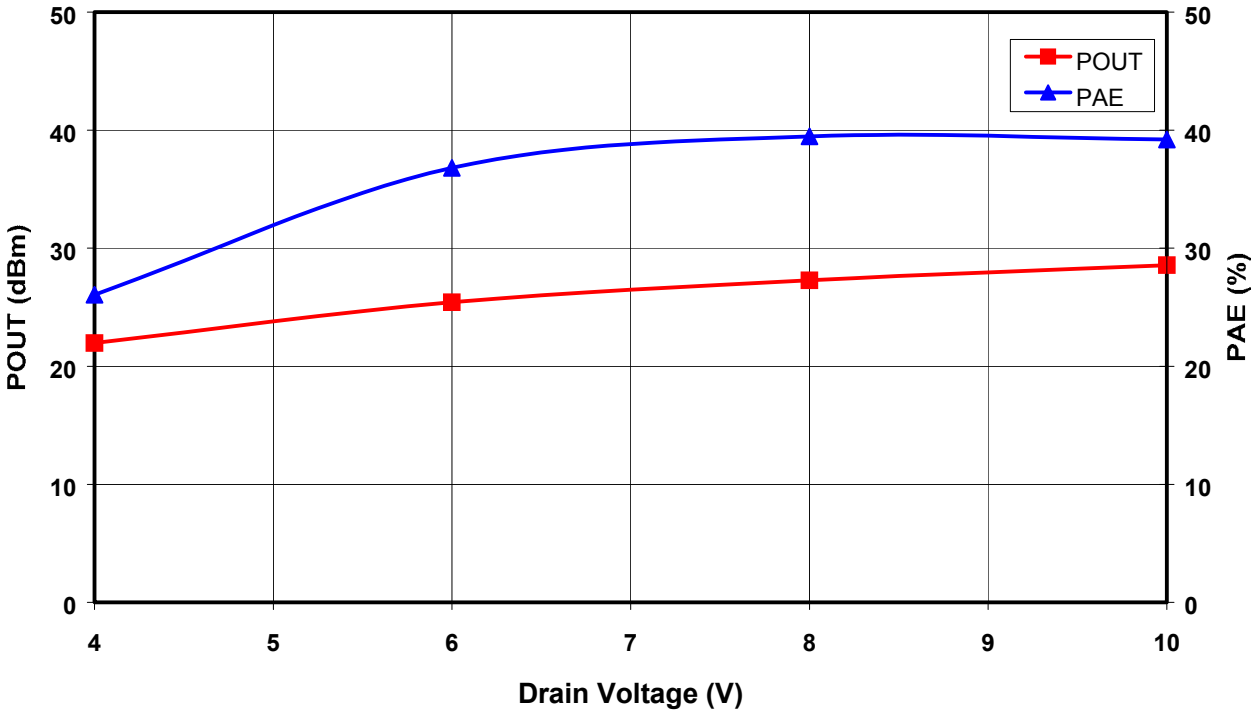

Figure 2. Saturated Output Power and Power Added Efficiency vs. Drain Voltage at f_o = 10 GHz.

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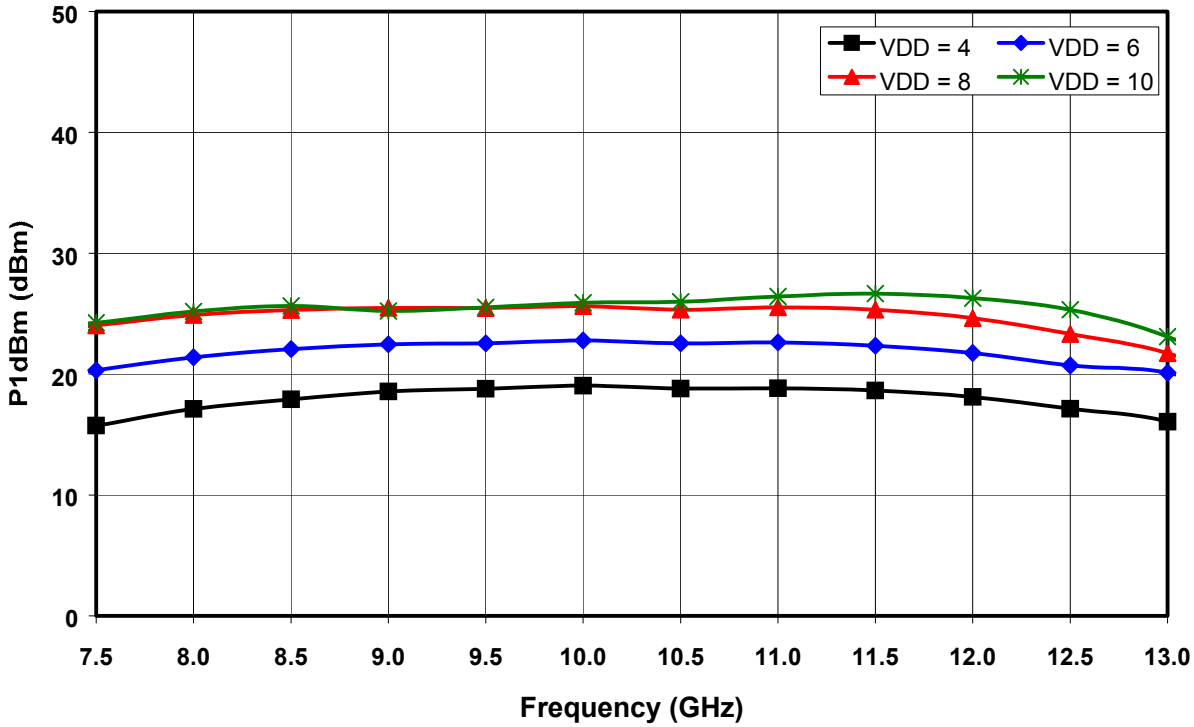

Figure 3. 1dB Compression Point vs. Drain Voltage

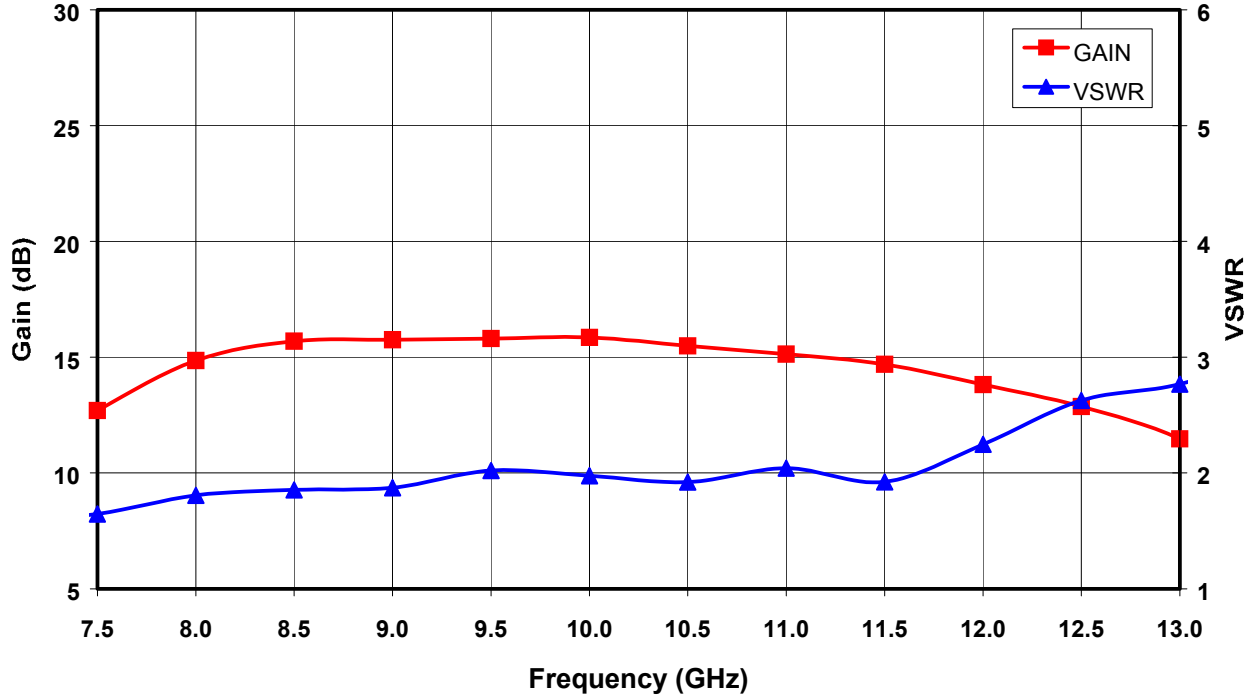

Figure 4. Small Signal Gain and Input VSWR vs. Frequency at V_{DD} = 10V.

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Mechanical Information

Chip Size: 2.480 x 1.580 x 0.075 mm (98 x 62 x 3 mils)

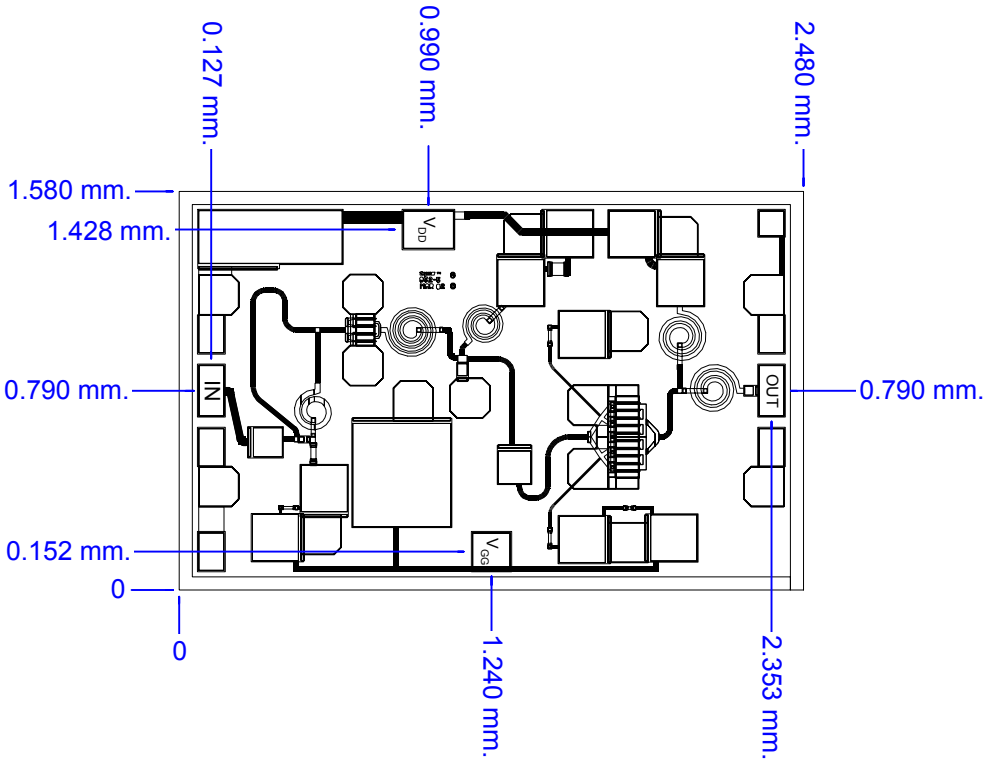

Figure 5. Die Layout

Chip edge to bond pad dimensions are shown to the center of the bond pad.

Bond Pad Dimensions

Pad	Size (µm)	Size (mils)
RF In and Out	100 x 200	4 x 8
DC Drain Supply Voltage VDD	200 x 150	8 x 6
DC Gate Supply Voltage VGG	150 x 150	6 x 6

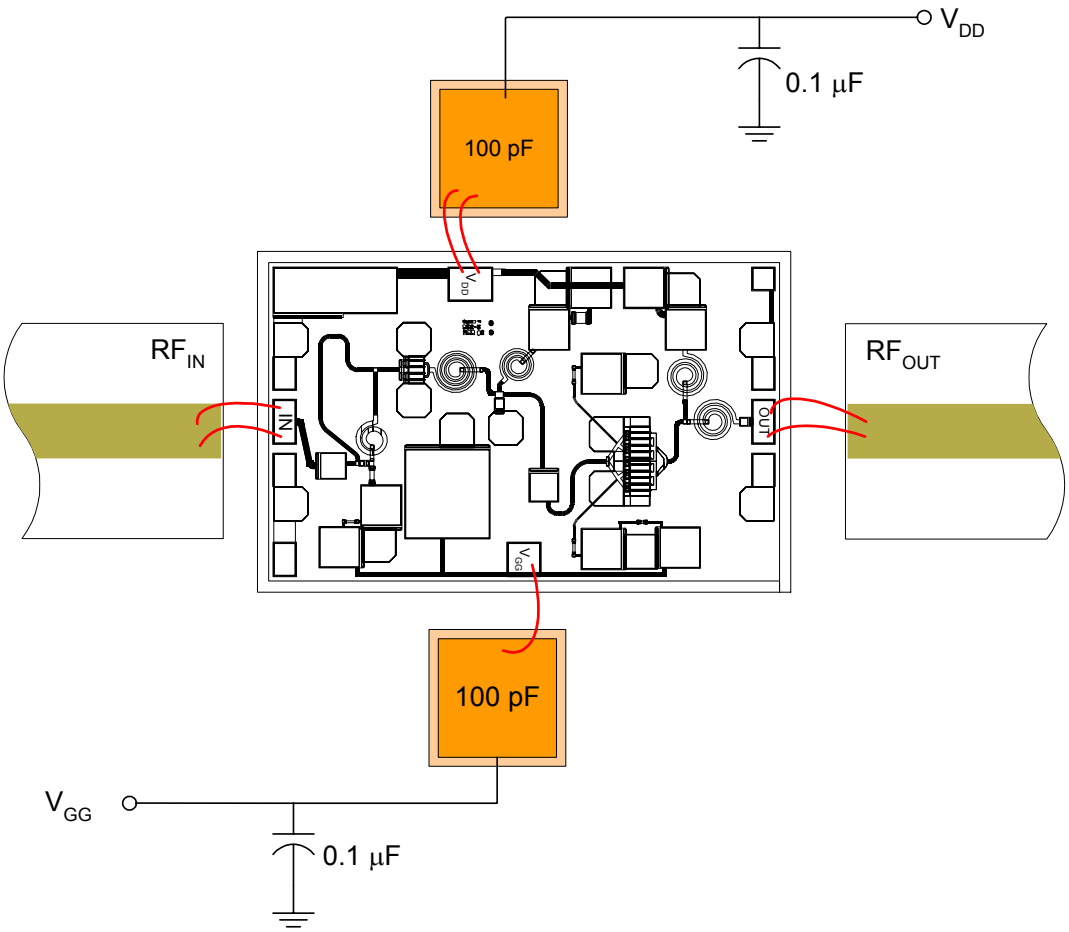

Figure 6. Recommended bonding diagram for pedestal mount.
Support circuitry typical of MMIC characterization fixture for CW testing.

Assembly Instructions:

Die attach: Use AuSn (80/20) 1-2 mil. preform solder. Limit time @ 300 °C to less than 5 minutes.

Wirebonding: Bond @ 160 °C using standard ball or thermal compression wedge bond techniques. For DC pad connections, use either ball or wedge bonds. For best RF performance, use wedge bonds of shortest length, although ball bonds are also acceptable.

Biasing Note: Must apply negative bias to V_{GG} before applying positive bias to V_{DD} to prevent damage to amplifier.